



# Influence of instrumental factors on Auger quantification applied to dispenser cathodes

JEAN-MICHEL ROQUAIS  
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## OUTLINE

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### Description of the cathodes

### Purpose of Auger measurements

### Auger systems set-up & typical spectra

### Comparison PHI CMA vs. SPECS HSA

- Angular differences and effects on signal intensity
- Choice of acquisition mode of HSA (FRR & FAT)

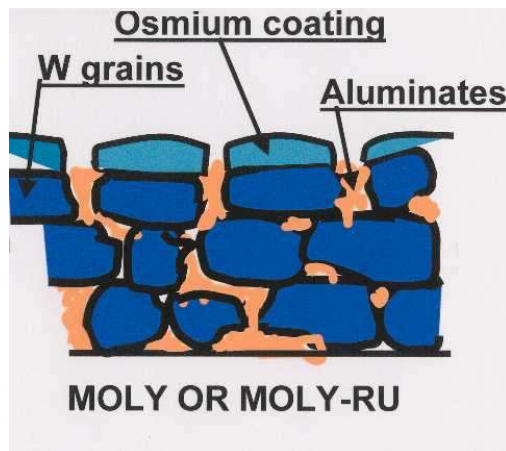
### Comparison between experiment and calculation

### Conclusion

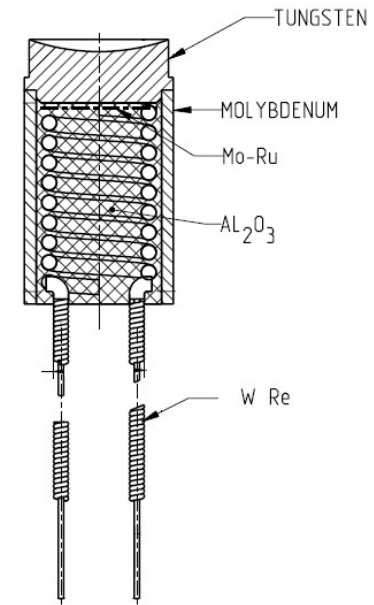
## Description of the cathodes

### M-type

- The cathode porous matrix is impregnated with 4-1-1 Ba, Ca aluminate



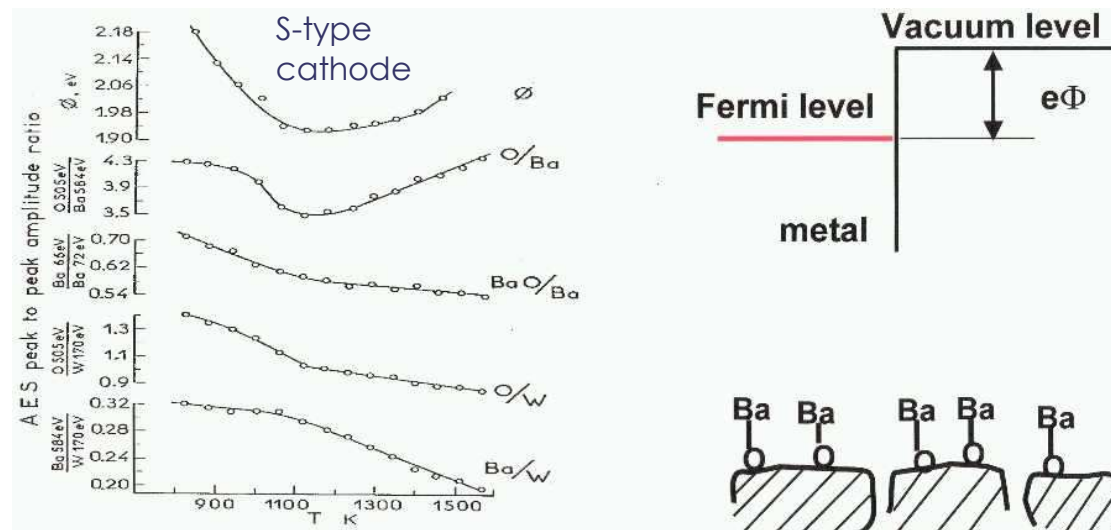
Cross-section



## Purpose of Auger measurements

### Link between surface composition and cathode emission

- See D. Brion, J.C. Tonnerre & A.M. Shroff Applications of Surface Science 16 (1983) 55-72
- Ba/W proportional to Ba coverage  $\theta$  of the surface (fraction of monolayer)



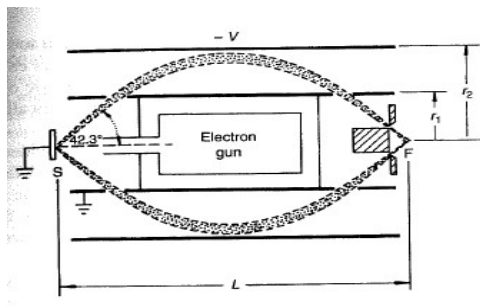
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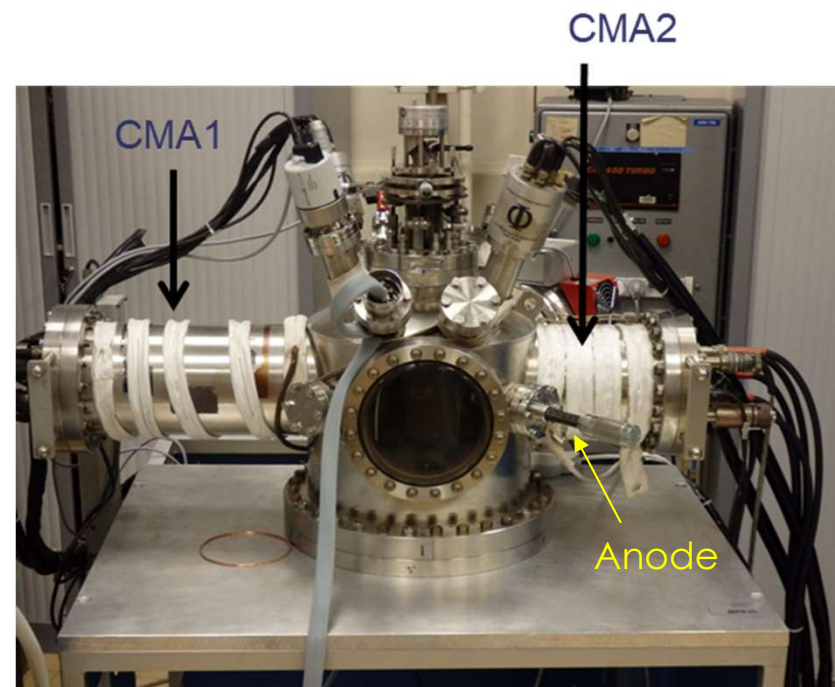
## Auger systems set-up & typical spectra

### PHI 545 from PHI

#### ➤ CMA(Cylindrical Mirror Analyzer)



- e gun co-axial with the cylinders
- Anode dedicated to measure electronic emission of the cathode under test



## Auger systems set-up & typical spectra

### Phoibos HSA from SPECS GmbH

#### ➤ H.S.A: Hemispherical Sector Analyzer

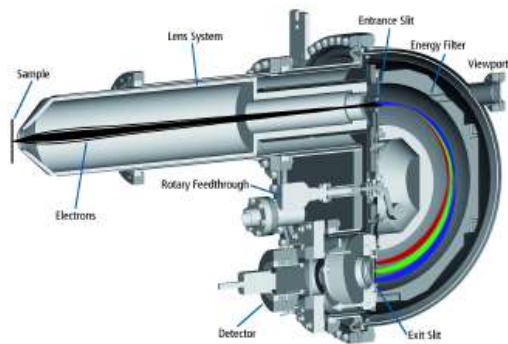
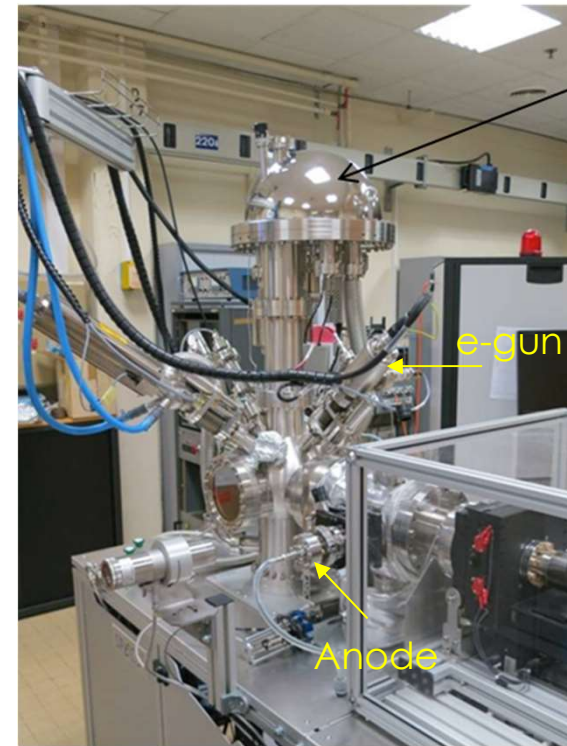


Figure 40: Cut-out view of PHOIBOS 100/150 analyzer

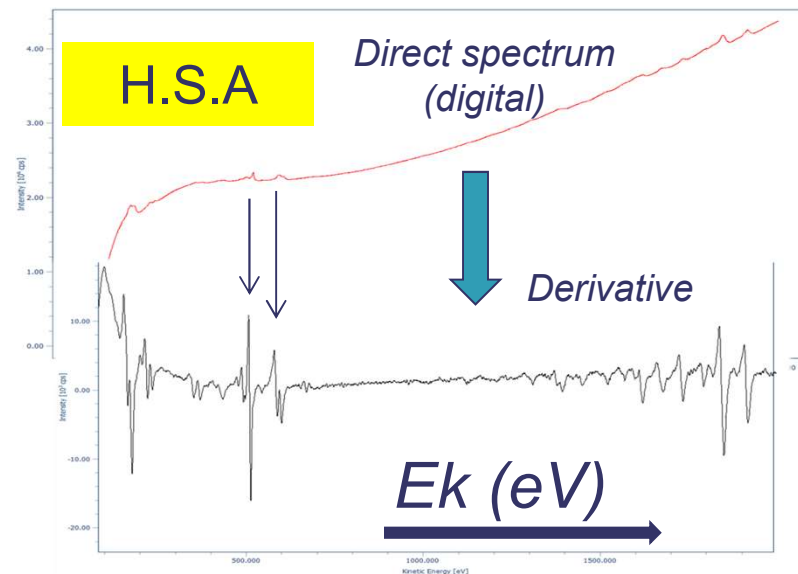
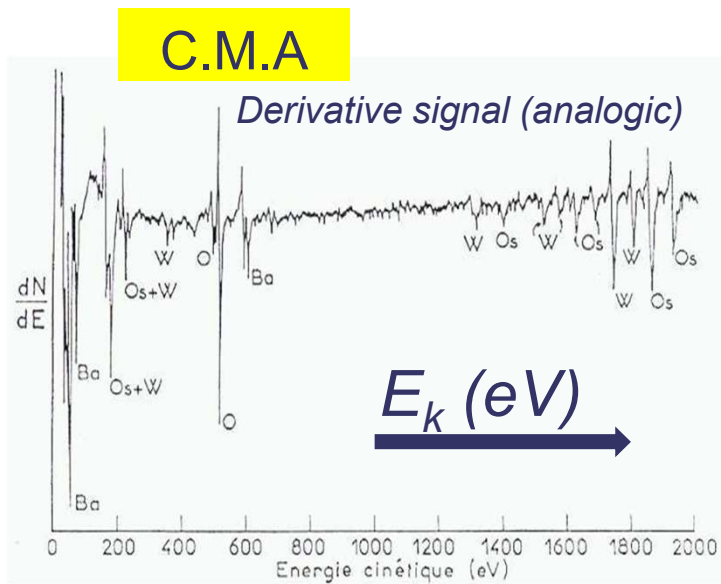
- e gun for Auger, X-Ray source for XPS
- Anode to measure electronic emission



Phoibos  
H.S.A

## Auger systems set-up & typical spectra

### Typical spectrum on cathode surface acquired at 1000 °CB



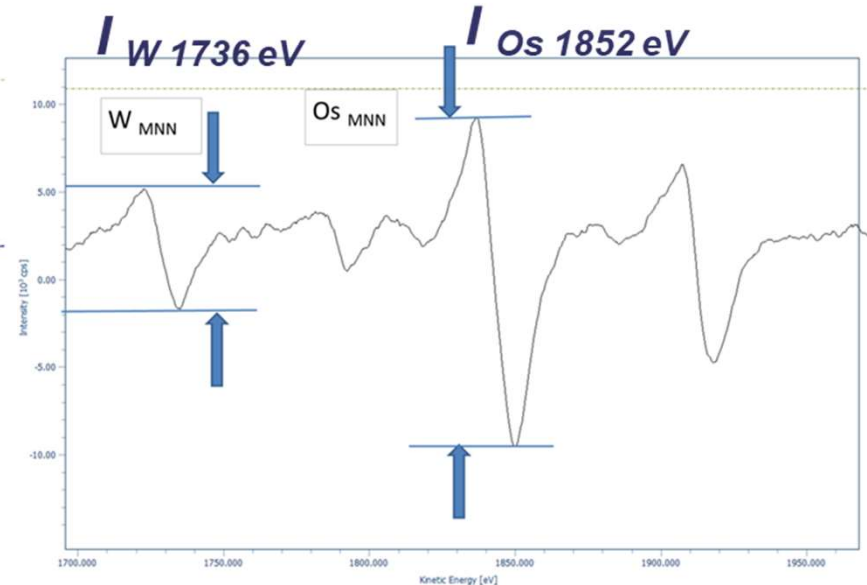
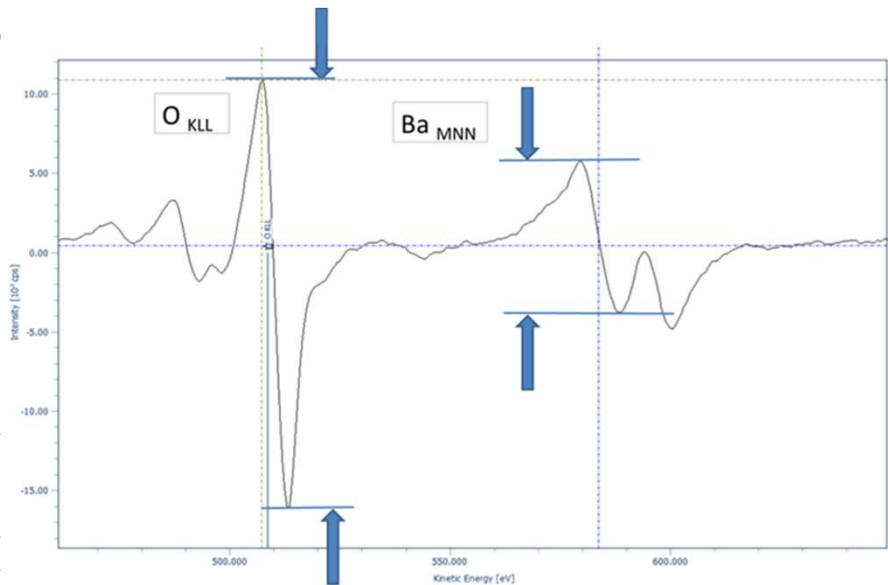
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# Auger systems set-up & typical spectra

## Quantification



$$O/Ba = I_{O\ 510\ eV} / I_{Ba\ 584\ eV}$$

$$Ba/*W_h = I_{Ba\ 584\ eV} / (I_{W\ 1736\ eV} + I_{Os\ 1852\ eV} / S_{rel.})$$



# Comparison PHI CMA/ SPECS HSA/ angular differences

## Geometry of Auger systems \*

	Electron Incidence angle $\alpha$ with respect to the sample surface normal $\vec{n}$	Electron emission angle $\theta$ with respect to the sample surface normal $\vec{n}$
PHI 545 (CMA/ Single pass)	30 °	$\theta_{\text{avg.}} \sim 50^\circ$
SPECS (HSA)	48 °	0 °

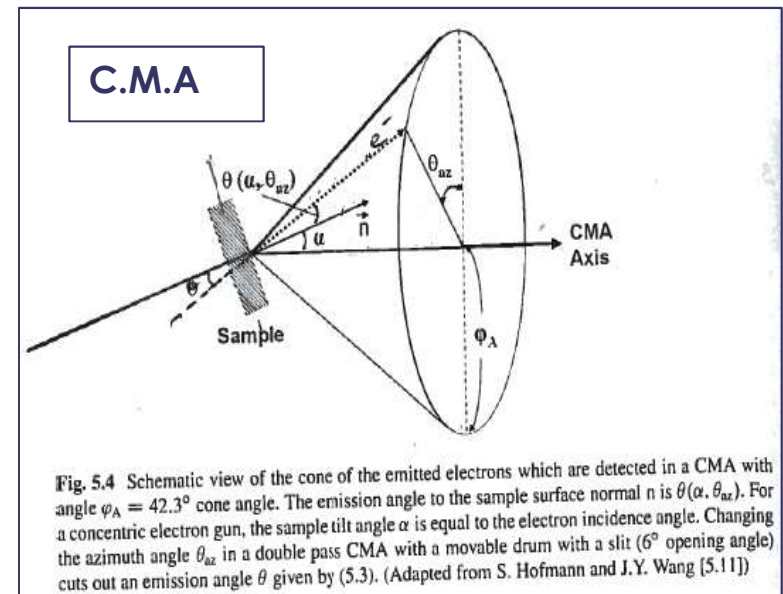
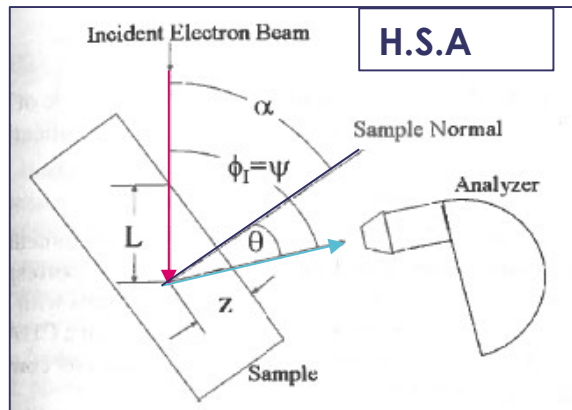


Fig. 5.4 Schematic view of the cone of the emitted electrons which are detected in a CMA with angle  $\phi_A = 42.3^\circ$  cone angle. The emission angle to the sample surface normal  $n$  is  $\theta(\alpha, \theta_{\text{az}})$ . For a concentric electron gun, the sample tilt angle  $\alpha$  is equal to the electron incidence angle. Changing the azimuth angle  $\theta_{\text{az}}$  in a double pass CMA with a movable drum with a slit ( $6^\circ$  opening angle) cuts out an emission angle  $\theta$  given by (5.3). (Adapted from S. Hofmann and J.Y. Wang [5.11])

\* Siegfried Hofmann "Auger-and X-Ray Photoelectron Spectroscopy in Materials Science" Springer 49

## Comparison PHI CMA/ SPECS HSA/ angular effect on intensities

### Approximation of thin overlayer A on substrate B (from \*Hofmann § 4.4.3.2):

- $E_A$ : kinetic energy of signal from A
- $E_B$ : kinetic energy of signal from B
- $S_A, S_B$ : elemental sensitivity factors (not instrument linked)
- $\lambda_A, E(A)$ : attenuation length of signal of A at  $E_A$
- $\theta$ : electron emission angle



**Auger intensities ratio  $I_A/I_B$  depends on incident angle  $\alpha$  and emission angle  $\theta$**

$$\frac{I_A}{I_B} = \frac{S_A}{S_B} * \frac{1 + r_{B,U(A)}}{1 + r_{A,U(A)}} * \left[ \exp\left[\frac{d}{\lambda_{A,E(A)} \cos \theta} \left(\frac{E_A}{E_B}\right)^{0,75}\right] - \exp\left[\frac{-d}{\lambda_{A,E(A)} \cos \theta} \left(1 - \left(\frac{E_A}{E_B}\right)^{0,75}\right)\right] \right]$$

Cancels at  
instruments  
comparison

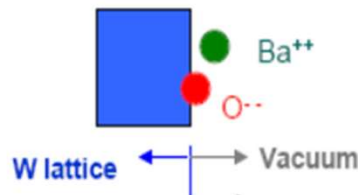
$\alpha$  influence  
Backscattered term close  
for SPECS and PHI systems

$\theta$  influence

## Comparison PHI CMA/ SPECS HSA/ angular effect on intensities

### Approximation of thin overlayer A on substrate B (from \*Hofmann § 4.4.3.2):

- Surface layer A = O-Ba monolayer
- Substrate B = W-Os
- $\lambda_{590} \sim 4,8$  mono-layers



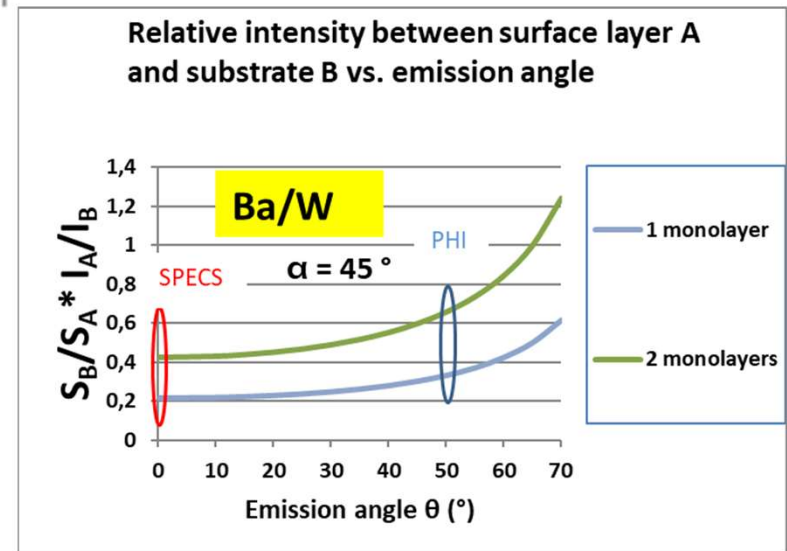
Emission angles:  $\theta_{\text{SPECS}} \neq \theta_{\text{PHI}}$

$$\rightarrow I_A/I_B (\text{SPECS}) \neq I_A/I_B (\text{PHI})$$

Calculation for cathode leads to:

$$\text{Ba/W}_{(\theta = 50^\circ/\text{PHI})} = 1,56 * \text{Ba/W}_{(\theta = 0^\circ/\text{SPECS})}$$

\* G. A. Haas et al. Applied Surface Science 24 (1985) 430-446



## Choice of acquisition mode of HSA

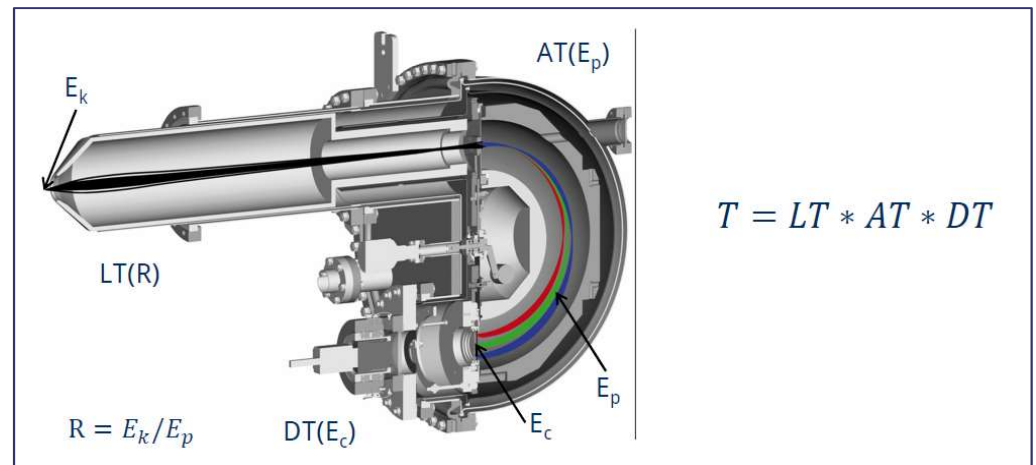
Signal intensity  $I$  is proportional to analyzer transmission function  $T$

H.S.A: 3 sections determine  $T$

- Lens section (= retarding section)
- Analyzer (hemispheres)
- Detector (MultiChannel Plates)

Electron kinetic energy

- $E_k$  at Lens section entrance
- Pass energy  $E_{\text{pass}} = E_k/R$  at hemispheres entrance
- Conversion energy  $E_c = E_{\text{bias}} + E_{\text{pass}}$  (a bias voltage is applied between hemispheres exit and detector)



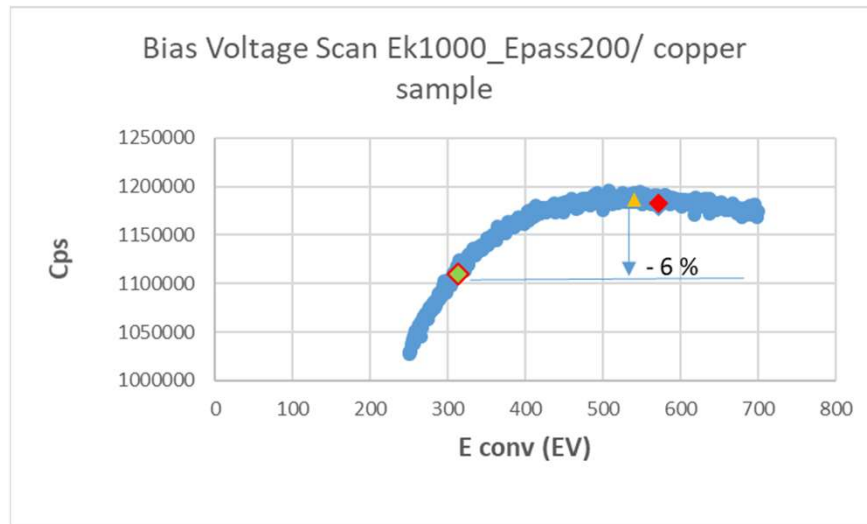
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## Choice of acquisition mode of HSA

### Detector efficiency (Signal intensity vs. E conversion)

- $E_{\text{conv.}} = E_{\text{bias}} + E_{\text{pass}}$
- In FRR mode (Fixed Retarding Ratio)  $E_{\text{pass}} = E_k/R$
- $DT(E_c)$  not constant and  $E_{\text{conv.}}$  varies with  $E_k \rightarrow DT(E_k)$  not constant



		FRR5	
	Ekin (eV)	Epass (eV)	Econv (eV)
<b>Ba584</b>	584	116,8	<b>316,8</b>
<b>W1736</b>	1736	347,2	<b>547,2</b>
<b>Os1850</b>	1850	370	<b>570</b>

## Transmission function $T$

### FRR vs. FAT

- FAT (Fixed Analyzer Transmission):  $E_{\text{pass}}$  is constant
- $E_{\text{pass}}$  chosen to match quantification results in FRR

	Advantage	Drawback
FRR mode	<ul style="list-style-type: none"><li>• <math>\Delta E/E = \text{cste}</math> like for the CMA (PHI)</li></ul>	<b>Detector ageing:</b> If drift of detector gain → impact on quantification
FAT mode	No influence of detector on quantification when only Auger <u>peak ratios</u> are under consideration	Need to verify Lens Transmission on a regular basis (check applied voltages )

## Comparison between experiment and calculation

### Determination of « transposition » factor between PHI and SPECS

- Comparison of cathodes from the same material batches
- The ratios are average values of 5 spectra/ cath.

### Results

- O/Ba ratio is the same in PHI and SPECS
- Ba/Wh ratio shift between SPECS and PHI
- The experimental transposition factor matches the calculated one
- The difference of  $e^-$  emission angle ( $\cos\theta$  factor) explains mainly the shift

		O/Ba (Measured)	Ba/Wh (Measured)	
PHI	Avg. 15 Cath.	2,93	0,341	
SPECS /FAT	Avg. 9 Cath.	2,83	0,207	X 1,65
Experimental transposition factor				
PHI/SPECS FAT		1	1,65	
Theoretical transposition SPECS/PHI :				
Cos $\theta$ (SPECS)/ Cos $\theta$ (PHI)			1,56	

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## Comparison between experiment and calculation

### Statistical results

- Following transposition tests, comparison of 29 cath. in SPECS vs. 29 cath. In PHI.
- Equivalent results are obtained in SPECS and PHI
- Typical J0 is 11 A/cm<sup>2</sup> at 1000 °CB.

Statistical confirmation		O/Ba (Measured)	Ba/Wh (Measured)
PHI	Avg. 29 Cath.	2.88	0,345
SPECS/FAT	Avg. 29 Cath.	2,98	* 0,341
* Experimental transposition factor applied			

## Conclusion

### Transposition from PHI to SPECS system was completed successfully:

- Acquisition mode « FAT » was retained for quantification (not impacted by detector efficiency)
- A transposition factor between PHI and SPECS systems has been calculated based on differences in systems geometries
- The transposition factor has been confirmed by comparative measurements on cathodes in both Auger systems

### After completion of transposition, statistical results on 29 cathodes assess the transposition factor

## Acknowledgements

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*Thank you for your attention !*